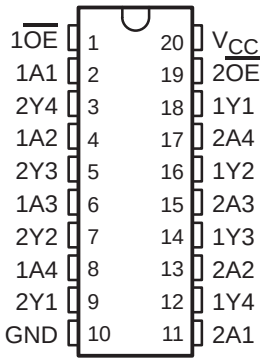
# SN74ALVC244
# OCTAL BUFFER/DRIVER WITH 3-STATE OUTPUTS

SCES188 – FEBRUARY 1999

- ***EPIC***™ **(Enhanced-Performance Implanted CMOS) Submicron Process**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Package Options Include Plastic Small-Outline (DW, NS), Thin Very Small-Outline (DGV), and Thin Shrink Small-Outline (PW) Packages**

**DGV, DW, NS, OR PW PACKAGE**
**(TOP VIEW)**




## description

This octal buffer/line driver is designed for 1.65-V to 3.6-V $V_{CC}$ operation.

The SN74ALVC244 is organized as two 4-bit line drivers with separate output-enable ($\overline{OE}$) inputs. When $\overline{OE}$ is low, the device passes data from the A inputs to the Y outputs. When $\overline{OE}$ is high, the outputs are in the high-impedance state.

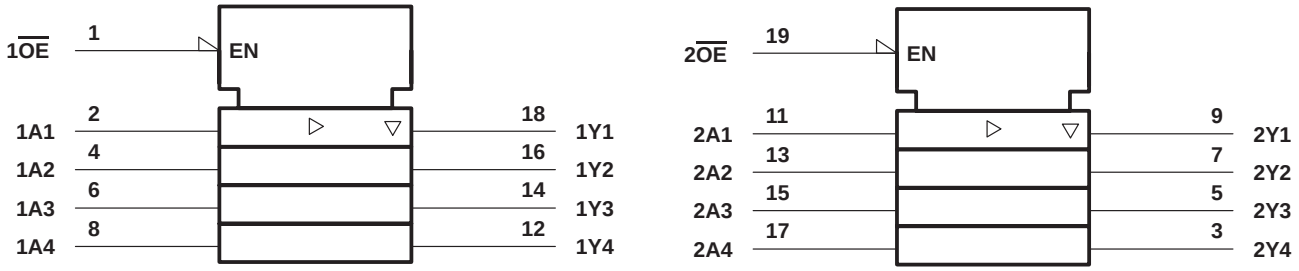
To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to $V_{CC}$ through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN74ALVC244 is characterized for operation from –40°C to 85°C.

**FUNCTION TABLE**
**(each buffer)**

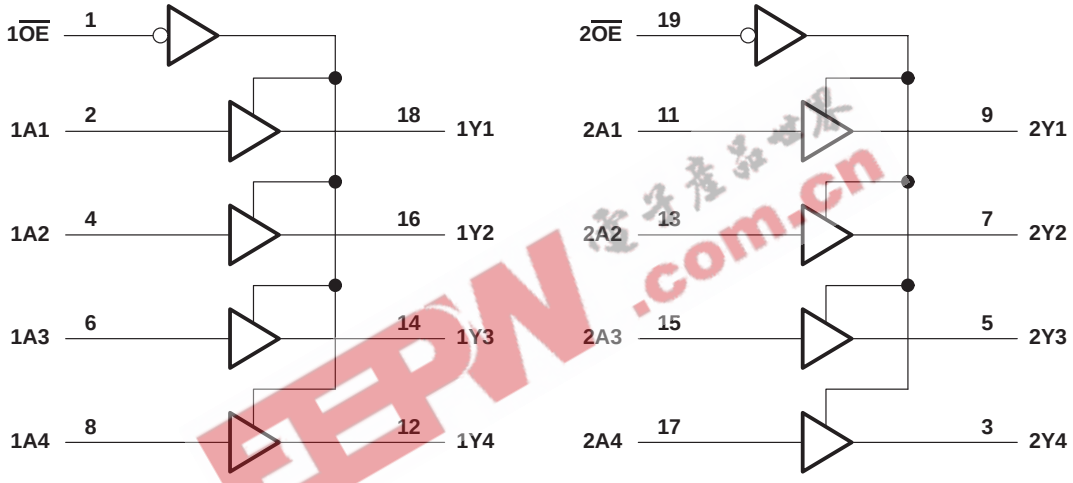
| INPUTS | | OUTPUT |
|---|---|---|
| $\overline{OE}$ | A | Y |
| L | H | H |
| L | L | L |
| H | X | Z |

## logic symbol†




† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

## logic diagram (positive logic)




## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, $V_{CC}$ . . . . . –0.5 V to 4.6 V
Input voltage range, $V_I$ (see Note 1) . . . . . –0.5 V to 4.6 V
Output voltage range, $V_O$ (see Notes 1 and 2) . . . . . –0.5 V to $V_{CC}$ + 0.5 V
Input clamp current, $I_{IK}$ ($V_I$ < 0) . . . . . –50 mA
Output clamp current, $I_{OK}$ ($V_O$ < 0) . . . . . –50 mA
Continuous output current, $I_O$ . . . . . ±50 mA
Continuous current through $V_{CC}$ or GND . . . . . ±100 mA
Package thermal impedance, $\theta_{JA}$ (see Note 3): DGV package . . . . . 146°C/W
DW package . . . . . 97°C/W
NS package . . . . . 100°C/W
PW package . . . . . 128°C/W
Storage temperature range, $T_{stg}$ . . . . . –65°C to 150°C

‡ Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. This value is limited to 4.6 V maximum.
3. The package thermal impedance is calculated in accordance with JESD 51.

## recommended operating conditions (see Note 4)

| | | | MIN | MAX | UNIT |
|---|---|---|---|---|---|
| $V_{CC}$ | Supply voltage | | 1.65 | 3.6 | V |
| $V_{IH}$ | High-level input voltage | $V_{CC}$ = 1.65 V to 1.95 V | 0.65 × $V_{CC}$ | | V |
| | | $V_{CC}$ = 2.3 V to 2.7 V | 1.7 | | |
| | | $V_{CC}$ = 2.7 V to 3.6 V | 2 | | |
| $V_{IL}$ | Low-level input voltage | $V_{CC}$ = 1.65 V to 1.95 V | | 0.35 × $V_{CC}$ | V |
| | | $V_{CC}$ = 2.3 V to 2.7 V | | 0.7 | |
| | | $V_{CC}$ = 2.7 V to 3.6 V | | 0.8 | |
| $V_I$ | Input voltage | | 0 | $V_{CC}$ | V |
| $V_O$ | Output voltage | | 0 | $V_{CC}$ | V |
| $I_{OH}$ | High-level output current | $V_{CC}$ = 1.65 V | | –4 | mA |
| | | $V_{CC}$ = 2.3 V | | –12 | |
| | | $V_{CC}$ = 2.7 V | | –12 | |
| | | $V_{CC}$ = 3 V | | –24 | |
| $I_{OL}$ | Low-level output current | $V_{CC}$ = 1.65 V | | 4 | mA |
| | | $V_{CC}$ = 2.3 V | | 12 | |
| | | $V_{CC}$ = 2.7 V | | 12 | |
| | | $V_{CC}$ = 3 V | | 24 | |
| $\Delta t/\Delta v$ | Input transition rise or fall rate | | | 5 | ns/V |
| $T_A$ | Operating free-air temperature | | –40 | 85 | °C |

NOTE 4: All unused inputs of the device must be held at $V_{CC}$ or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

## electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | $V_{CC}$ | MIN | TYP† | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $V_{OH}$ | | $I_{OH}$ = –100 µA | | 1.65 V to 3.6 V | $V_{CC}$–0.2 | | | V |
| | | $I_{OH}$ = –4 mA | | 1.65 V | 1.2 | | | |
| | | $I_{OH}$ = –6 mA | | 2.3 V | 2 | | | |
| | | $I_{OH}$ = –12 mA | | 2.3 V | 1.7 | | | |
| | | | | 2.7 V | 2.2 | | | |
| | | | | 3 V | 2.4 | | | |
| | | $I_{OH}$ = –24 mA | | 3 V | 2 | | | |
| $V_{OL}$ | | $I_{OL}$ = 100 µA | | 1.65 V to 3.6 V | | | 0.2 | V |
| | | $I_{OL}$ = 4 mA | | 1.65 V | | | 0.45 | |
| | | $I_{OL}$ = 6 mA | | 2.3 V | | | 0.4 | |
| | | $I_{OL}$ = 12 mA | | 2.3 V | | | 0.7 | |
| | | | | 2.7 V | | | 0.4 | |
| | | $I_{OL}$ = 24 mA | | 3 V | | | 0.55 | |
| $I_I$ | | $V_I$ = $V_{CC}$ or GND | | 3.6 V | | | ±5 | µA |
| $I_{OZ}$ | | $V_O$ = $V_{CC}$ or GND | | 3.6 V | | | ±10 | µA |
| $I_{CC}$ | | $V_I$ = $V_{CC}$ or GND, | $I_O$ = 0 | 3.6 V | | | 10 | µA |
| $\Delta I_{CC}$ | | One input at $V_{CC}$ – 0.6 V, | Other inputs at $V_{CC}$ or GND | 3 V to 3.6 V | | | 750 | µA |
| $C_i$ | Control inputs | $V_I$ = $V_{CC}$ or GND | | 3.3 V | | 4.5 | | pF |
| | Data inputs | | | | | 4.5 | | |
| $C_o$ | Outputs | $V_O$ = $V_{CC}$ or GND | | 3.3 V | | 7.5 | | pF |

† All typical values are at $V_{CC}$ = 3.3 V, $T_A$ = 25°C.

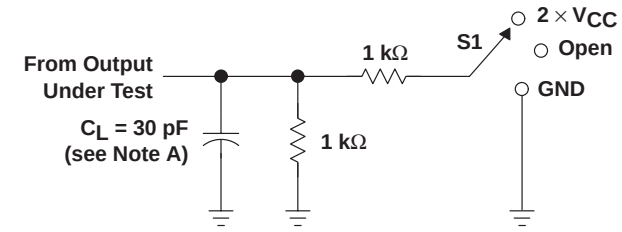
## switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 3)

| PARAMETER | FROM (INPUT) | TO (OUTPUT) | $V_{CC}$ = 1.8 V ± 0.15 V | | $V_{CC}$ = 2.5 V ± 0.2 V | | $V_{CC}$ = 2.7 V | | $V_{CC}$ = 3.3 V ± 0.3 V | | UNIT |
|---|---|---|---|---|---|---|---|---|---|---|---|
| | | | MIN | MAX | MIN | MAX | MIN | MAX | MIN | MAX | |
| $t_{pd}$ | A | Y | 1 | 4.4 | 1 | 3.1 | | 3.1 | 1.1 | 2.8 | ns |
| $t_{en}$ | $\overline{OE}$ | Y | 1.8 | 6.9 | 1.5 | 5.4 | | 5.3 | 1.5 | 4.5 | ns |
| $t_{dis}$ | $\overline{OE}$ | Y | 1.8 | 5.9 | 1 | 4.1 | | 4.4 | 1.7 | 4.2 | ns |

## operating characteristics, $T_A$ = 25°C

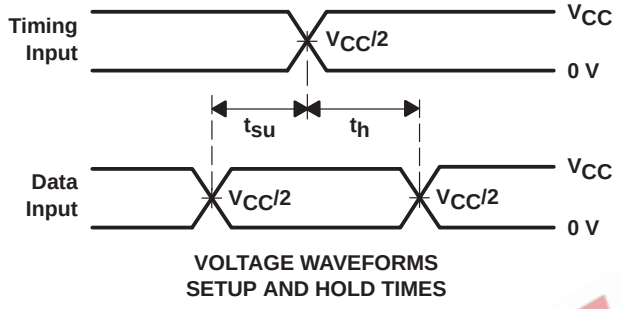
| PARAMETER | | | TEST CONDITIONS | $V_{CC}$ = 1.8 V | $V_{CC}$ = 2.5 V | $V_{CC}$ = 3.3 V | UNIT |
|---|---|---|---|---|---|---|---|
| | | | | TYP | TYP | TYP | |
| $C_{pd}$ | Power dissipation capacitance per buffer/driver | Outputs enabled | $C_L$ = 0, f = 10 MHz | 22 | 23 | 26 | pF |
| | | Outputs disabled | | 1 | 1 | 1 | |

## PARAMETER MEASUREMENT INFORMATION
## $V_{CC}$ = 1.8 V ± 0.15 V

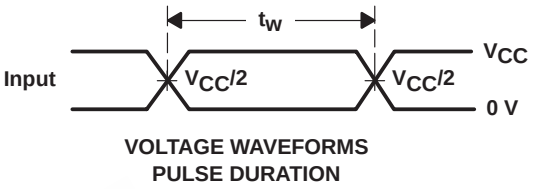



LOAD CIRCUIT

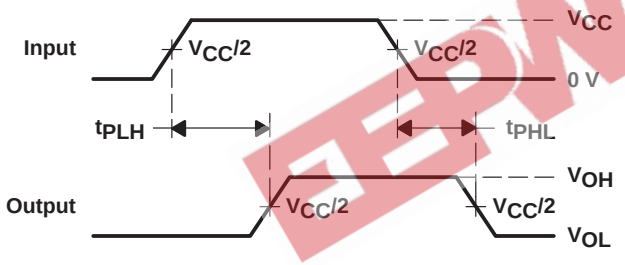
| TEST | S1 |
|---|---|
| $t_{pd}$<br>$t_{PLZ}/t_{PZL}$<br>$t_{PHZ}/t_{PZH}$ | Open<br>2 × $V_{CC}$<br>GND |



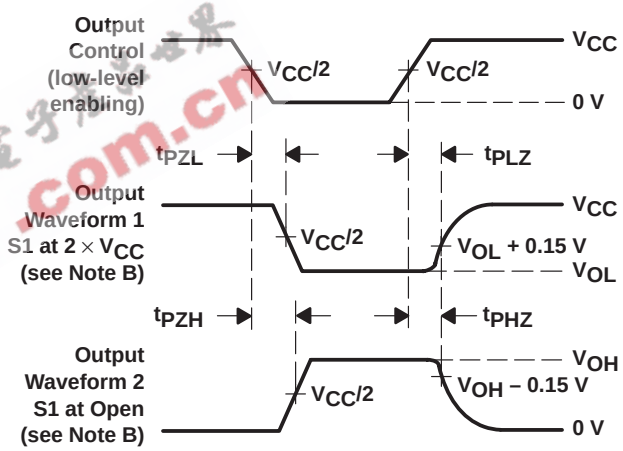

VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES




VOLTAGE WAVEFORMS
PULSE DURATION




VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

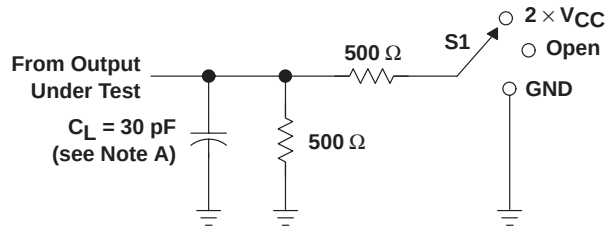



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. $C_L$ includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O$ = 50 Ω, $t_r$ ≤ 2 ns, $t_f$ ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. $t_{PLZ}$ and $t_{PHZ}$ are the same as $t_{dis}$.
F. $t_{PZL}$ and $t_{PZH}$ are the same as $t_{en}$.
G. $t_{PLH}$ and $t_{PHL}$ are the same as $t_{pd}$.

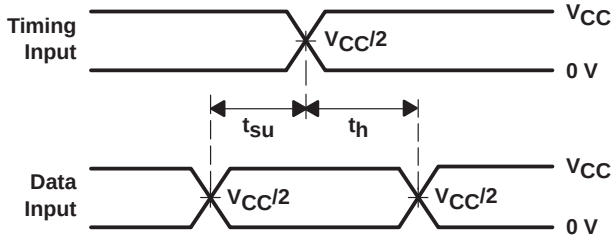
**Figure 1. Load Circuit and Voltage Waveforms**

## PARAMETER MEASUREMENT INFORMATION
## $V_{CC}$ = 2.5 V ± 0.2 V

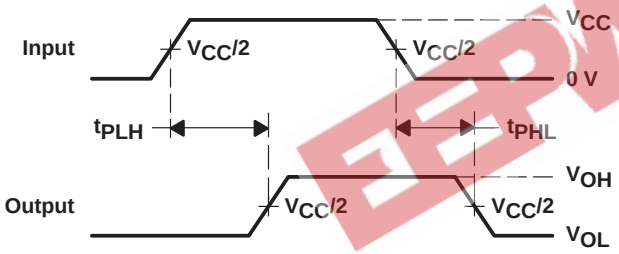



| TEST | S1 |
|---|---|
| $t_{pd}$<br>$t_{PLZ}/t_{PZL}$<br>$t_{PHZ}/t_{PZH}$ | Open<br>2 × $V_{CC}$<br>GND |

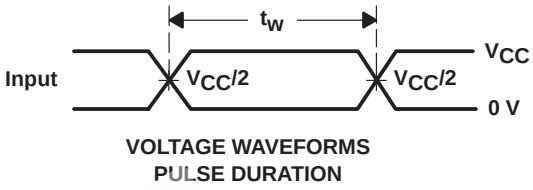
LOAD CIRCUIT



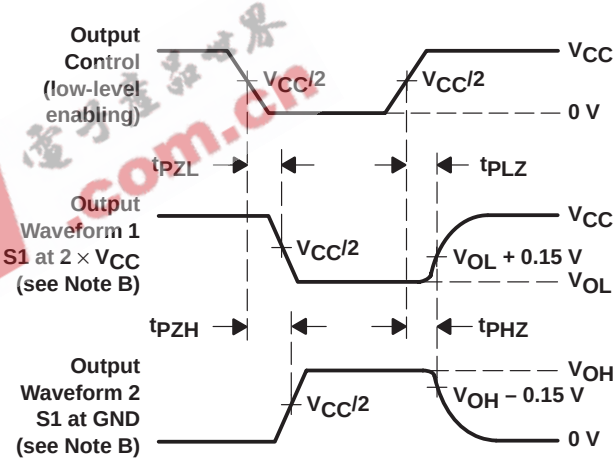

VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES




VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES




VOLTAGE WAVEFORMS
PULSE DURATION

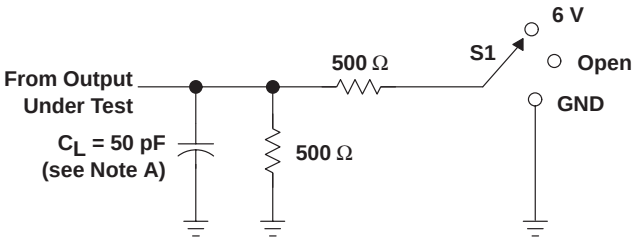



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. $C_L$ includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O$ = 50 Ω, $t_r$ ≤ 2 ns, $t_f$ ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. $t_{PLZ}$ and $t_{PHZ}$ are the same as $t_{dis}$.
F. $t_{PZL}$ and $t_{PZH}$ are the same as $t_{en}$.
G. $t_{PLH}$ and $t_{PHL}$ are the same as $t_{pd}$.

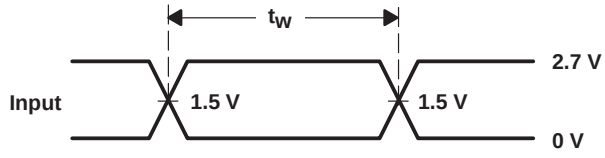
**Figure 2. Load Circuit and Voltage Waveforms**

## PARAMETER MEASUREMENT INFORMATION
## $V_{CC}$ = 2.7 V AND 3.3 V ± 0.3 V

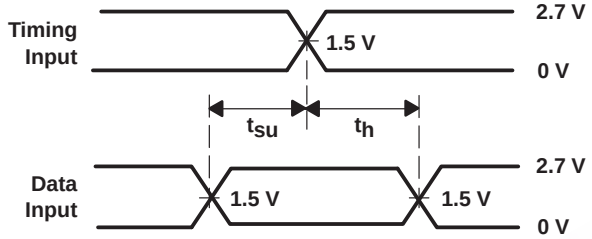



| TEST | S1 |
|---|---|
| $t_{pd}$<br>$t_{PLZ}/t_{PZL}$<br>$t_{PHZ}/t_{PZH}$ | Open<br>6 V<br>GND |

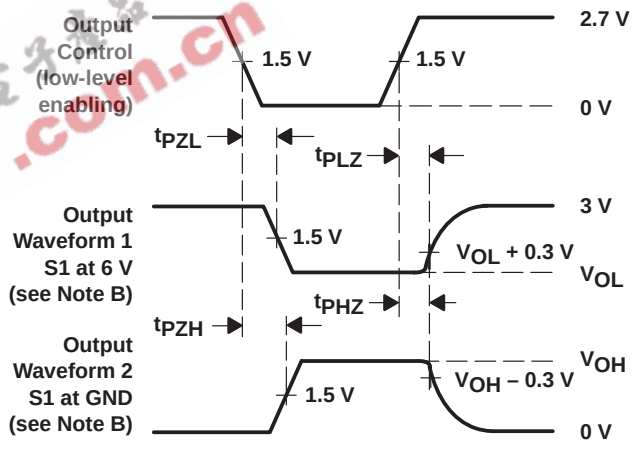
LOAD CIRCUIT



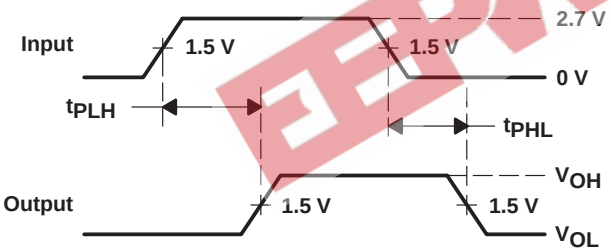

VOLTAGE WAVEFORMS
PULSE DURATION




VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES




VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES




VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

NOTES: A. $C_L$ includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O$ = 50 Ω, $t_r$ ≤ 2.5 ns, $t_f$ ≤ 2.5 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. $t_{PLZ}$ and $t_{PHZ}$ are the same as $t_{dis}$.
F. $t_{PZL}$ and $t_{PZH}$ are the same as $t_{en}$.
G. $t_{PLH}$ and $t_{PHL}$ are the same as $t_{pd}$.

**Figure 3. Load Circuit and Voltage Waveforms**

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